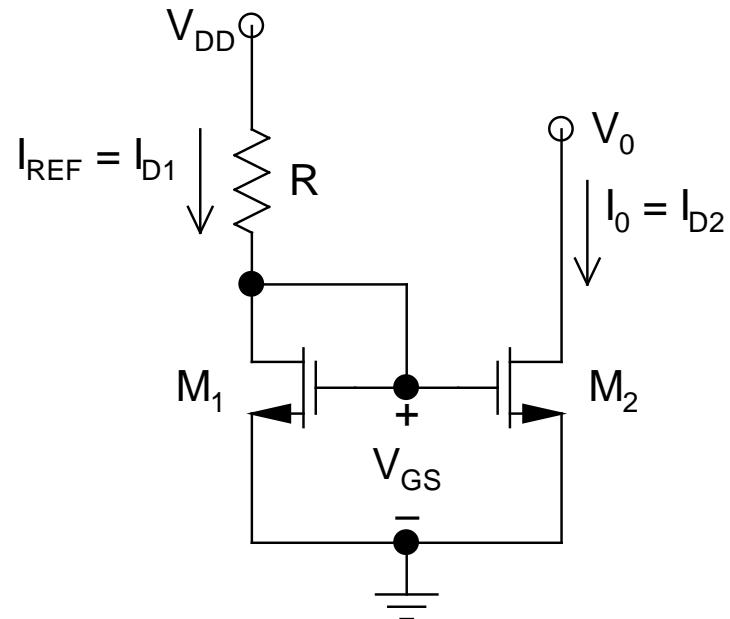


- *Simple NMOS CM:*

- $V_{GS1} = V_{GS2} = V_{GS}$
- M_1 has its *D and G shorted* $\Rightarrow V_{GD1} = 0$
 \Rightarrow *always in saturation*,
since $V_{DS1} > V_{GT1}$
- Known as *diode-connected MOSFET*



- Even though $I_G = 0$, the analysis is slightly more cumbersome than simple BJT CM

- *In general, for NMOS (PMOS), the body terminal is always connected to the most negative (positive) potential available in the circuit to ensure that SB and DB junctions never get forward biased*
- *Both M_1 and M_2 have their body terminals grounded* $\Rightarrow V_{SB1} = V_{SB2} = 0$
 - $V_{TN1} = V_{TN01}$ and $V_{TN2} = V_{TN02}$
- Thus, neglecting CLM:

$$I_{REF} = I_{D1} = \frac{k'_{N1}}{2} \left(\frac{W}{L} \right)_1 \left(V_{GS} - V_{TN01} \right)^2$$

- For a *given* V_{DD} and R , the equation has **2 unknowns**: I_{D1} and V_{GS}
- Need *another equation* for *unique solution*, which is the *load line equation*:

$$I_{D1} = (V_{DD} - V_{GS})/R$$

- *Simultaneous solution* of these *two equations* would give a *unique solution* for I_{D1} and V_{GS}
 - *Caution: 2 roots, out of which, one will be unphysical*
- So far, we have *neglected CLM*, which we would include soon!

➤ Now:

$$V_{GS} = V_{TN01} + \sqrt{\frac{2I_{REF}}{k'_{N1}(W/L)_1}} = V_{TN02} + \sqrt{\frac{2I_0}{k'_{N2}(W/L)_2}}$$

➤ Thus:

$$I_0 = \frac{k'_{N2}(W/L)_2}{2} \left[(V_{TN01} - V_{TN02}) + \sqrt{\frac{2I_{REF}}{k'_{N1}(W/L)_1}} \right]^2$$

➤ This is the *exact expression* of I_0 , *without making any assumptions/approximations whatsoever*

➤ Now, if $V_{TN01} = V_{TN02} = V_{TN0}$, and

$$k'_{N1} = k'_{N2} = k'_N :$$

$$I_0 = \frac{(W/L)_2}{(W/L)_1} I_{REF}$$

➤ *Very similar* to BJT CM, but with a *big difference*:

- *In BJT CM, this ratio could only be an integer*
- *In MOS CM, no such restriction exists: $(W/L)_2$ can be $>$, $=$, or $<$ $(W/L)_1 \Rightarrow$ any arbitrary current ratio can be obtained*

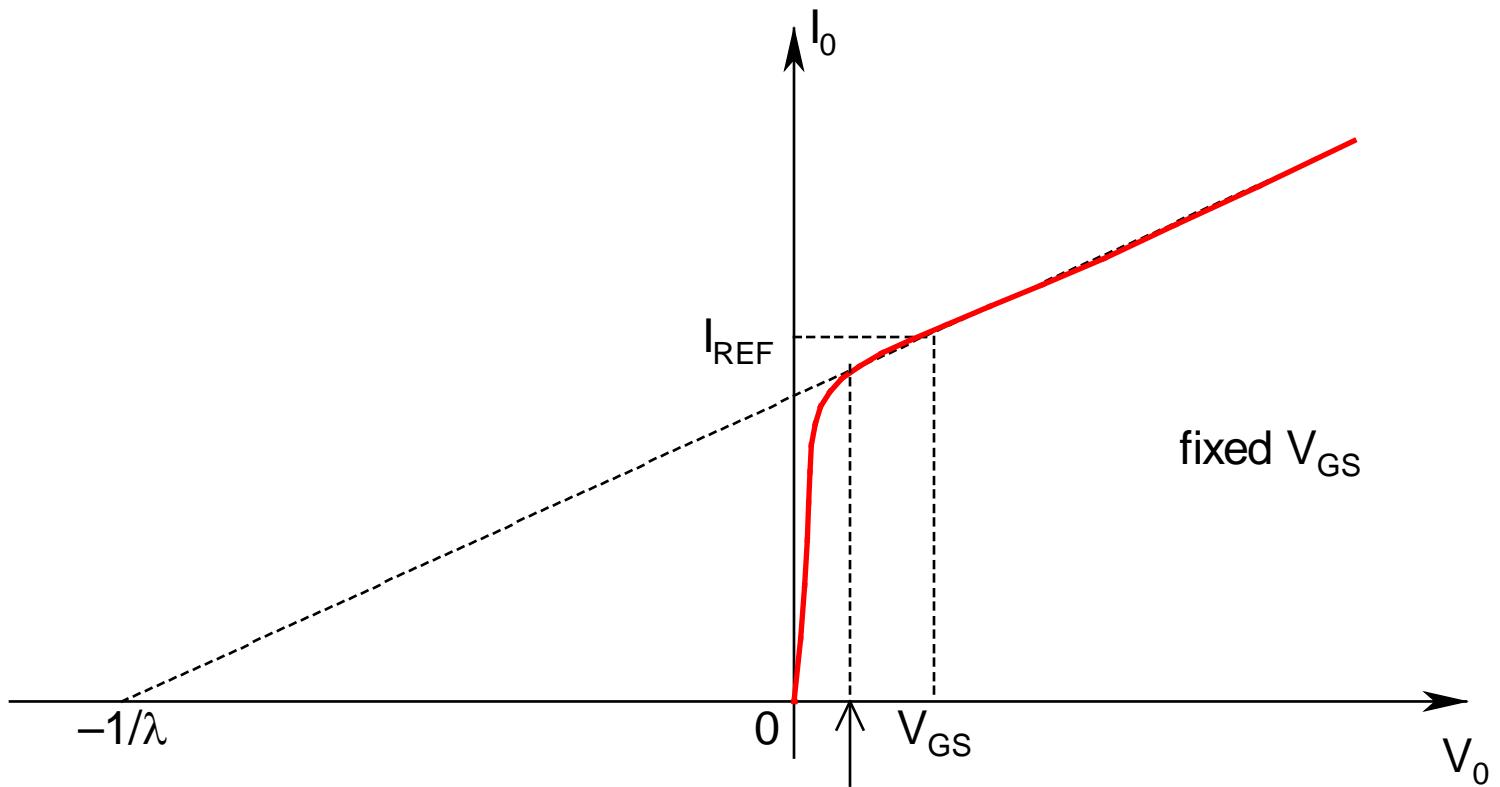
- Finally, if $(W/L)_2 = (W/L)_1$:
 $I_0 = I_{REF} \Rightarrow \text{Current Mirror!}$
- Two MOSFETs are deemed to constitute a *matched pair*, if they have *same* V_{TN0} , γ , ϕ_F , λ , and k'_N
 - Note that all of these are *process parameters*
 - *(W/L) is NOT a process parameter*, since it's under *designer's control*
 - *If (W/L) s are also same, then the pair is known as perfectly matched*

- **Systematic Error:**

- Even if M_1 and M_2 are *perfectly matched*, still I_0 *may not equal* I_{REF} !
- Recall:

$$I_D = \frac{k_N}{2} V_{GT}^2 (1 + \lambda V_{DS})$$

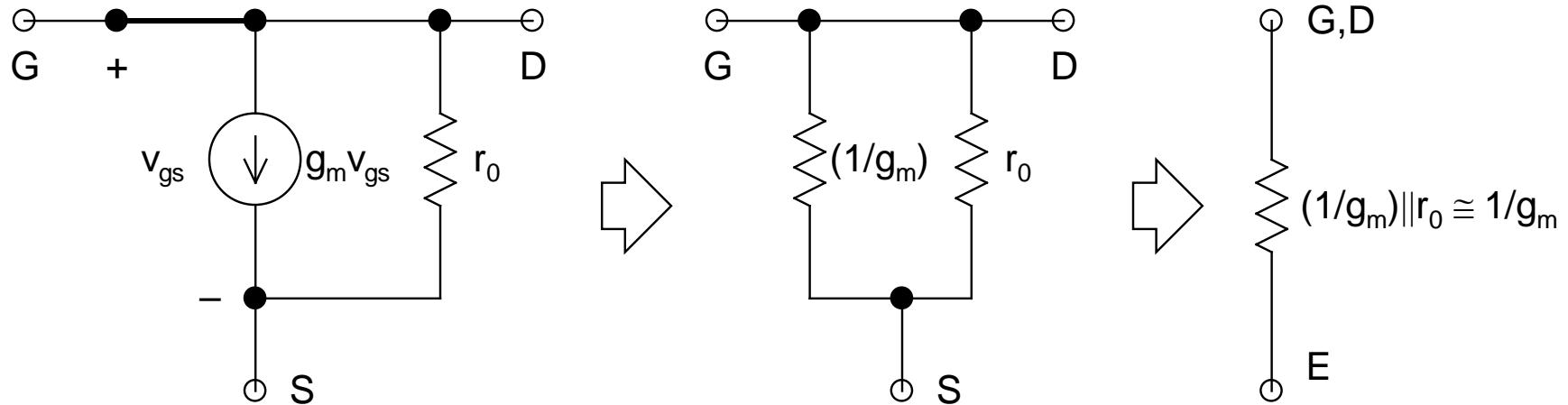
- Thus:
$$\frac{I_0}{I_{REF}} = \frac{1 + \lambda V_{DS2}}{1 + \lambda V_{DS1}} = \frac{1 + \lambda V_0}{1 + \lambda V_{GS}}$$
- Therefore, $I_0 = I_{REF}$ *only when* $V_0 = V_{GS}$



$V_{0,min} = V_{DS2(sat)}$
(lowest allowed value $\approx 3V_T$)

- ***Output Resistance R_0 :***

➤ First, *investigate M_1*



➤ The *small-signal equivalent* consists simply of $1/g_m$, which is similar to r_D for *diodes*

- Hence the name *diode-connected transistor*

- *For the complete circuit:*

➤ *Left part of the circuit has no source*

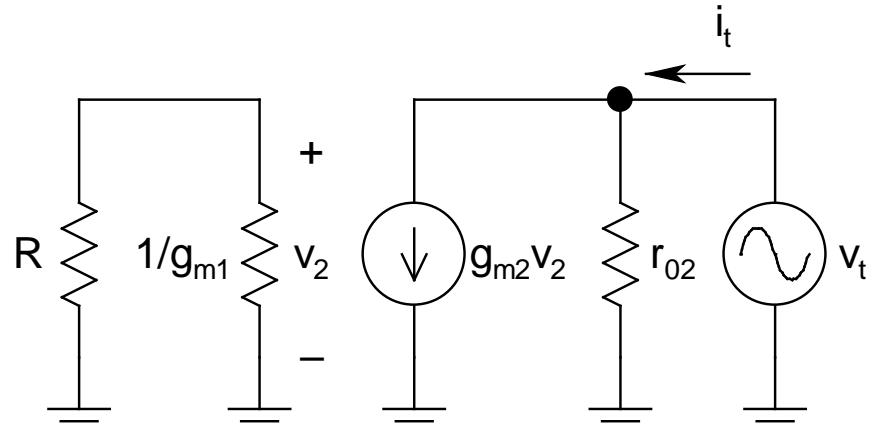
$$\Rightarrow v_2 = 0$$

$$\Rightarrow g_{m2}v_2 = 0$$

➤ Thus, $R_0 = v_t/i_t = r_{02} = 1/(\lambda I_0)$

➤ For a *good current source*, R_0 should be as large as possible (ideally infinite)

⇒ λ should be as small as possible and/or I_0 should be as small as possible

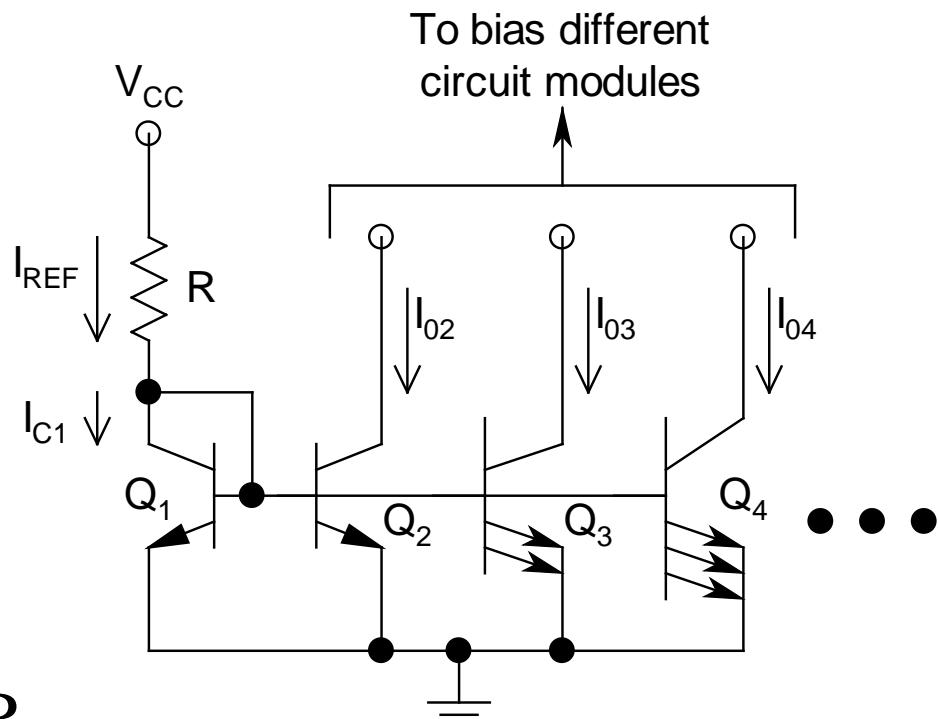


- ***Golden Rule for Calculation of R_o :***

- For a ***BJT*** (or ***MOSFET***):
 - With Emitter (or Source) ***grounded***
 - ***No electrical connection (feedback)*** between Collector (or Drain) and Base (or Gate)
 - ***Looking from*** the Collector (or Drain)
 - ❖ ***The only resistance seen will be the output resistance of the BJT (or MOSFET)***

- *n-p-n Current Repeater:*

- *Uses multi-emitter BJTs*
- *Maximum number of emitters = 4*
- *All emitters tied together*
- *All Qs have same V_{BE}*
- $I_{REF} = (V_{CC} - V_{BE})/R$



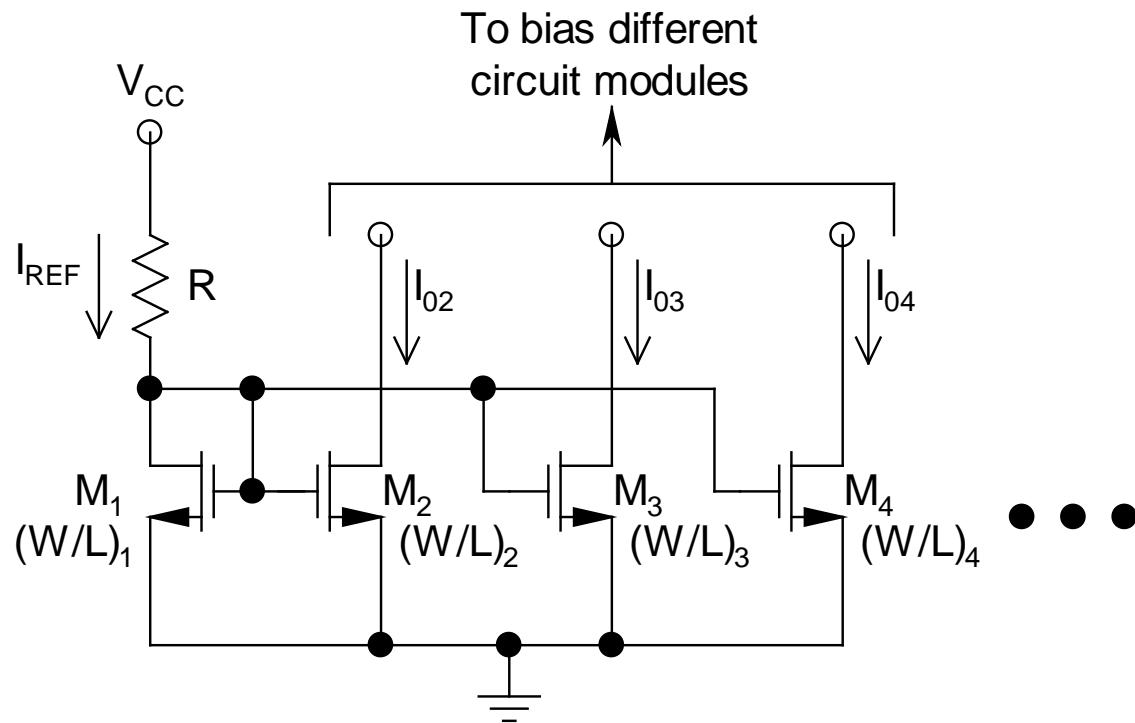
➤ **Neglecting I_B :**

$$I_{02} = I_{\text{REF}}, I_{03} = 2I_{\text{REF}}, I_{04} = 3I_{\text{REF}}, \dots$$

➤ **Limitations:**

- *Output current can never be a non-integer ratio of I_{REF} ⇒ no arbitrary scaling possible*
- **Loading Problem:**
 - ❖ I_{REF} not only supplies I_{C1} , but I_B s of all the Qs
 - ❖ As more Qs are added, I_B s will keep on increasing
 - ❖ I_{C1} starts to depart significantly from I_{REF}
 - ❖ It's actually NOT I_{REF} that's mirrored, BUT it's I_{C1}
 - ❖ A reduction in I_{C1} will affect all output currents
 - ❖ Hence, this circuit is not very popular

- **NMOS Current Repeater:**



➤ $I_{REF} = I_{D1} = (V_{DD} - V_{GS})/R$

$$I_{D1} = \frac{k'_N}{2} \left(\frac{W}{L} \right)_1 V_{GT}^2 \quad (\text{assuming } \lambda V_{DS} < 0.1)$$

➤ All Ms have same V_{GS} and are matched

$$\Rightarrow I_{0i} = \frac{(W/L)_i}{(W/L)_1} I_{REF} \quad (i = 2, 3, 4, \dots)$$

➤ Tremendous flexibility

- ❖ Any arbitrary current ratio can be obtained
- ❖ No loading effect
- ❖ Highly popular and universal choice